



12N40K-MT

Preliminary

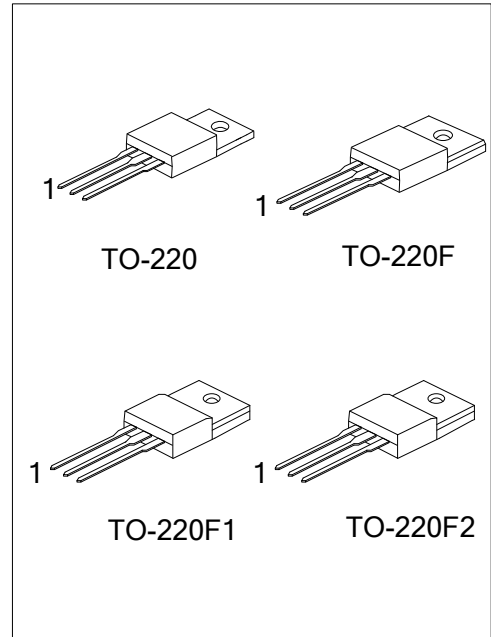
Power MOSFET

**12A, 400V N-CHANNEL
POWER MOSFET**

■ DESCRIPTION

The UTC **12N40K-MT** is an N-channel mode power MOSFET using UTC' s advanced technology to provide customers with planar stripe and DMOS technology. This technology specializes in allowing a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

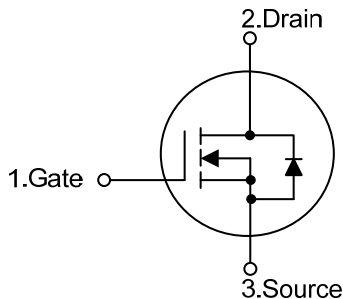
The UTC **12N40K-MT** is universally applied in electronic lamp ballast based on half bridge topology and high efficient switched mode power supply.



■ FEATURES

- * $R_{DS(ON)} < 0.47\Omega @ V_{GS} = 10V, I_D = 12A$
- * High switching speed
- * 100% avalanche tested

■ SYMBOL



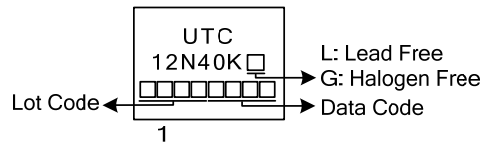
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12N40KL-TA3-T	12N40KG-TA3-T	TO-220	G	D	S	Tube
12N40KL-TF3-T	12N40KG-TF3-T	TO-220F	G	D	S	Tube
12N40KL-TF1-T	12N40KG-TF1-T	TO-220F1	G	D	S	Tube
12N40KL-TF2-T	12N40KG-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>12N40KL-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
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■ MARKING



FLYING 汎翔國際有限公司
www.flying1688.com

■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	400	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_c=25^\circ\text{C}$)	I_D	12	A
	Pulsed (Note 2)	I_{DM}	48	A
Single Pulsed Avalanche Energy		E_{AS}	474	mJ
Power Dissipation	TO-220	P_D	135	W
	TO-220F/TO-220F1		34	W
	TO-220F2			
Derate above 25°C	TO-220	P_D	1.08	W/ $^\circ\text{C}$
	TO-220F/TO-220F1		0.27	W/ $^\circ\text{C}$
	TO-220F2			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

4. $L=7.27\text{mH}$, $I_{AS}=11\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$

5. $I_{SD}\leq 11\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

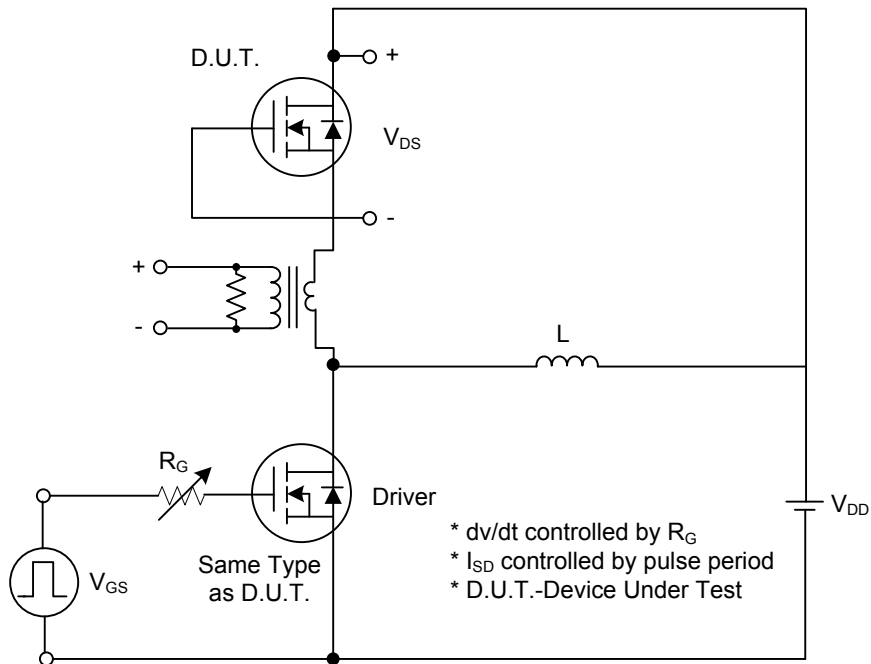
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.92	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.7	$^\circ\text{C}/\text{W}$
	TO-220F2			

■ ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$, unless otherwise noted)

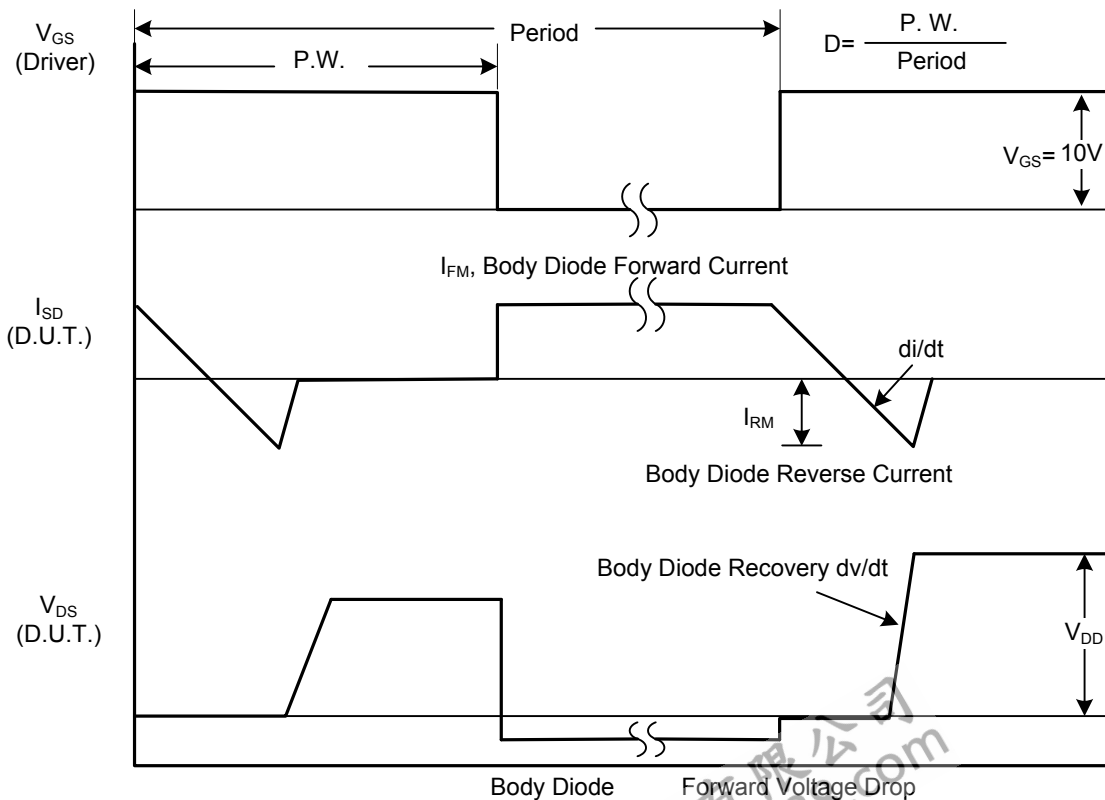
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	400			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=400\text{V}$, $V_{GS}=0\text{V}$			1	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+100	nA
	Reverse				-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=12\text{A}$			0.47	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		750		pF
Output Capacitance	C_{OSS}			153		pF
Reverse Transfer Capacitance	C_{RSS}			10		pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{DS}=50\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.3\text{A}$, $I_D=100\mu\text{A}$ (Note 1, 2)		31.3		nC
Gate-Source Charge	Q_{GS}			8.9		nC
Gate-Drain Charge	Q_{GD}			8.6		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DS}=30\text{V}$, $V_{GS}=10\text{V}$, $I_D=0.3\text{A}$, $R_G=25\Omega$ (Note 1, 2)		62		ns
Rise Time	t_R			94		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			162		ns
Fall-Time	t_F			96		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=12\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Maximum Body-Diode Continuous Current	I_S				12	A
Maximum Body-Diode Pulsed Current	I_{SM}				48	A

- Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

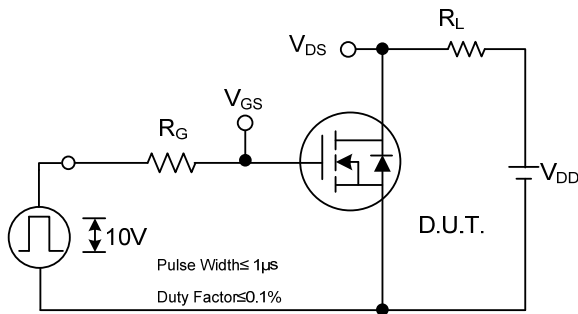


Peak Diode Recovery dv/dt Test Circuit

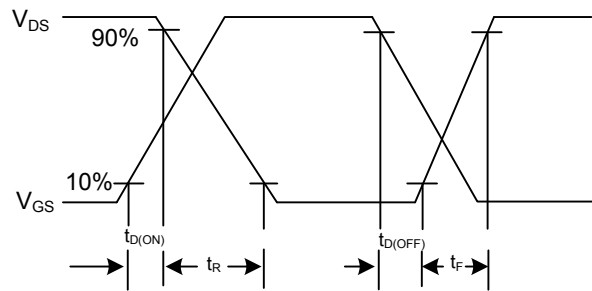


Peak Diode Recovery dv/dt Waveforms

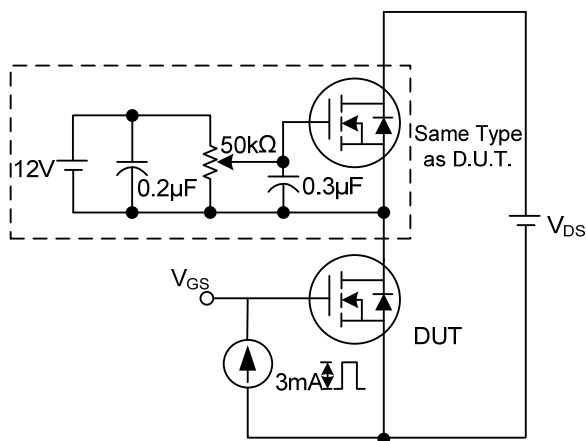
TEST CIRCUITS AND WAVEFORMS (Cont.)



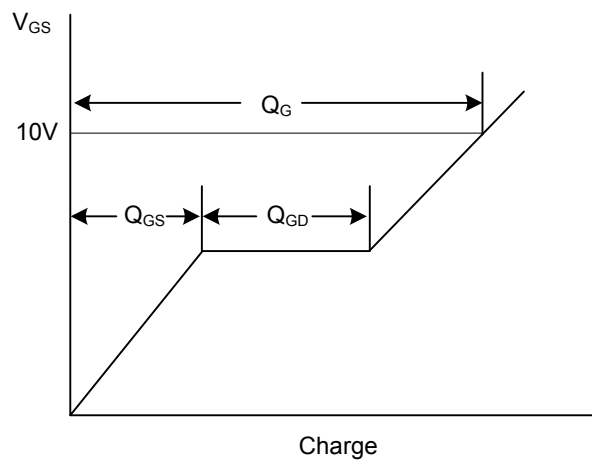
Switching Test Circuit



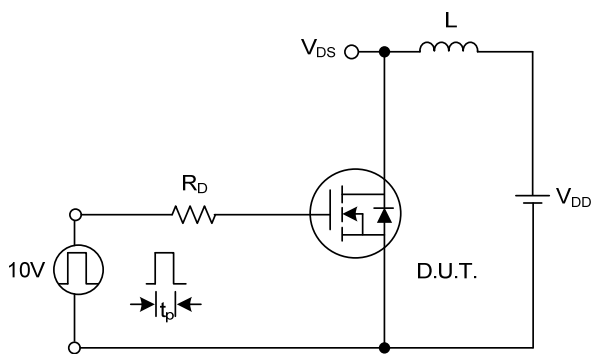
Switching Waveforms



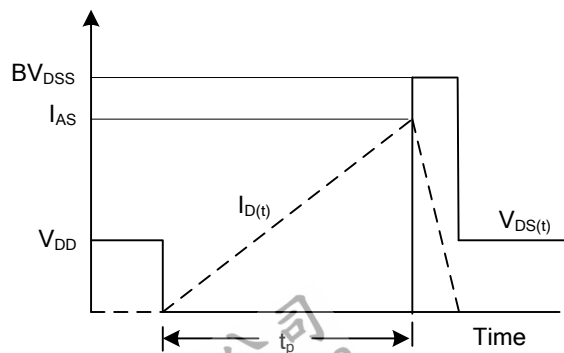
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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